**Din-Tek**
SEMICONDUCTOR

# P-Channel 30-V (D-S) MOSFET
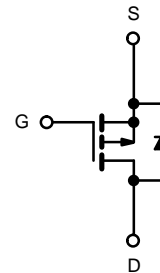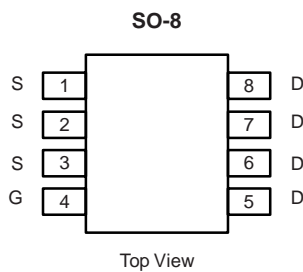
## PRODUCT SUMMARY

| $V_{DS}$ (V) | $R_{DS(on)}$ ($\Omega$) | $I_D$ (A) |
|---|---|---|
| - 30 | 0.042 at $V_{GS}$ = - 10 V | - 5.8 |
| | 0.055 at $V_{GS}$ = - 6 V | - 5.0 |
| | 0.060 at $V_{GS}$ = - 4.5 V | - 4.4 |

## FEATURES

- DT-Trench Power MOSFET
- Compliant to RoHS Directive 2002/95/EC

Pb
Pb-free

**RoHS**
COMPLIANT

**SO-8**

```
S  1      8  D
S  2      7  D
S  3      6  D
G  4      5  D
```

Top View

P-Channel MOSFET

## ABSOLUTE MAXIMUM RATINGS $T_A$ = 25 °C, unless otherwise noted

| Parameter | | Symbol | 10 s | Steady State | Unit |
|---|---|---|---|---|---|
| Drain-Source Voltage | | $V_{DS}$ | - 30 | | V |
| Gate-Source Voltage | | $V_{GS}$ | ± 20 | | |
| Continuous Drain Current ($T_J$ = 150 °C)[a] | $T_A$ = 25 °C | $I_D$ | - 5.8 | - 4.1 | A |
| | $T_A$ = 70 °C | | - 4.6 | - 3.2 | |
| Pulsed Drain Current | | $I_{DM}$ | - 30 | | |
| Continuous Source Current (Diode Conduction)[a] | | $I_S$ | - 2.3 | - 1.1 | |
| Maximum Power Dissipation[a] | $T_A$ = 25 °C | $P_D$ | 2.5 | 1.3 | W |
| | $T_A$ = 70 °C | | 1.6 | 0.8 | |
| Operating Junction and Storage Temperature Range | | $T_J$, $T_{stg}$ | - 55 to 150 | | °C |

## THERMAL RESISTANCE RATINGS

| Parameter | | Symbol | Typical | Maximum | Unit |
|---|---|---|---|---|---|
| Maximum Junction-to-Ambient[a] | t ≤ 10 s | $R_{thJA}$ | 40 | 50 | °C/W |
| | Steady State | | 70 | 95 | |
| Maximum Junction-to-Foot (Drain) | Steady State | $R_{thJF}$ | 24 | 30 | |

Notes:
a. Surface Mounted on 1" x 1" FR4 board.

**SPECIFICATIONS** $T_J$ = 25 °C, unless otherwise noted

| Parameter | Symbol | Test Conditions | Min. | Typ.[a] | Max. | Unit |
|---|---|---|---|---|---|---|
| **Static** | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}$, $I_D$ = - 250 µA | - 1.0 | | - 3.0 | V |
| Gate-Body Leakage | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ± 20 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V | | | - 1 | µA |
| | | $V_{DS}$ = - 30 V, $V_{GS}$ = 0 V, $T_J$ = 70 °C | | | - 5 | |
| On-State Drain Current[b] | $I_{D(on)}$ | $V_{DS} \leq$ - 10 V, $V_{GS}$ = - 10 V | - 20 | | | A |
| | | $V_{DS} \leq$ - 5 V, $V_{GS}$ = - 4.5 V | - 5 | | | |
| Drain-Source On-State Resistance[b] | $R_{DS(on)}$ | $V_{GS}$ = - 10 V, $I_D$ = - 5.8 A | | 0.042 | 0.055 | Ω |
| | | $V_{GS}$ = - 6 V, $I_D$ = - 5 A | | 0.055 | 0.070 | |
| | | $V_{GS}$ = - 4.5 V, $I_D$ = - 4.4 A | | 0.060 | 0.075 | |
| Forward Transconductance[b] | $g_{fs}$ | $V_{DS}$ = - 15 V, $I_D$ = - 5.8 A | | 13 | | S |
| Diode Forward Voltage[b] | $V_{SD}$ | $I_S$ = - 2.3 A, $V_{GS}$ = 0 V | | - 0.8 | - 1.1 | V |
| **Dynamic[a]** | | | | | | |
| Total Gate Charge | $Q_g$ | $V_{DS}$ = - 15 V, $V_{GS}$ = - 10 V, $I_D$ = - 3.5 A | | 16 | 24 | nC |
| Gate-Source Charge | $Q_{gs}$ | | | 2.3 | | |
| Gate-Drain Charge | $Q_{gd}$ | | | 4.5 | | |
| Gate Resistance | $R_g$ | | | 8.8 | | Ω |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{DD}$ = - 15 V, $R_L$ = 15 Ω  $I_D \cong$ - 1 A, $V_{GEN}$ = - 10 V, $R_g$ = 6 Ω | | 14 | 25 | ns |
| Rise Time | $t_r$ | | | 14 | 25 | |
| Turn-Off Delay Time | $t_{d(off)}$ | | | 42 | 70 | |
| Fall Time | $t_f$ | | | 30 | 50 | |
| Source-Drain Reverse Recovery Time | $t_{rr}$ | $I_F$ = - 1.2 A, dI/dt = 100 A/µs | | 30 | 60 | |

Notes:

a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq$ 300 µs, duty cycle $\leq$ 2 %.

*Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*
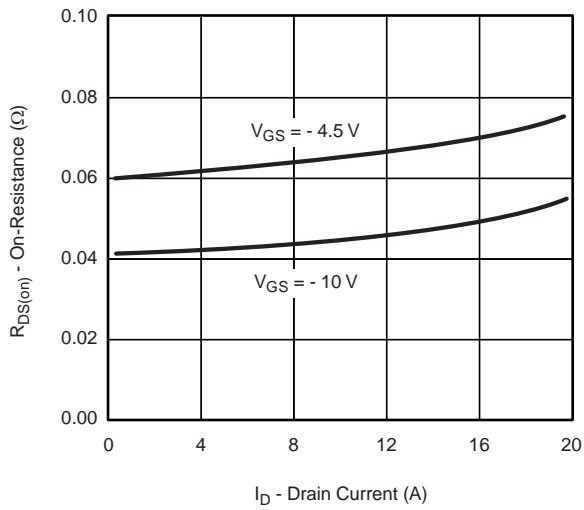
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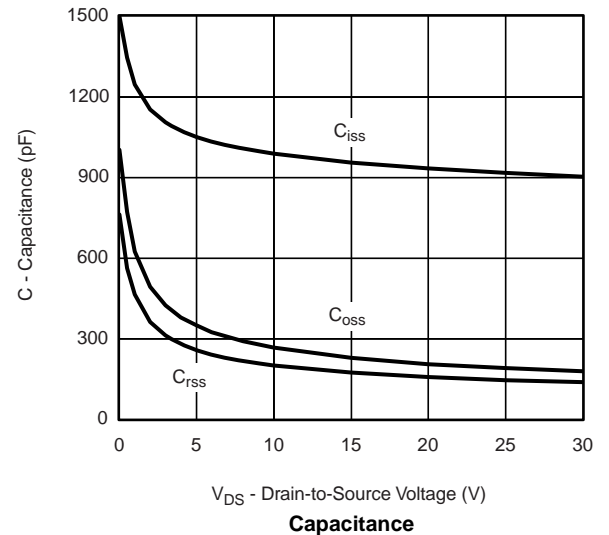**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted
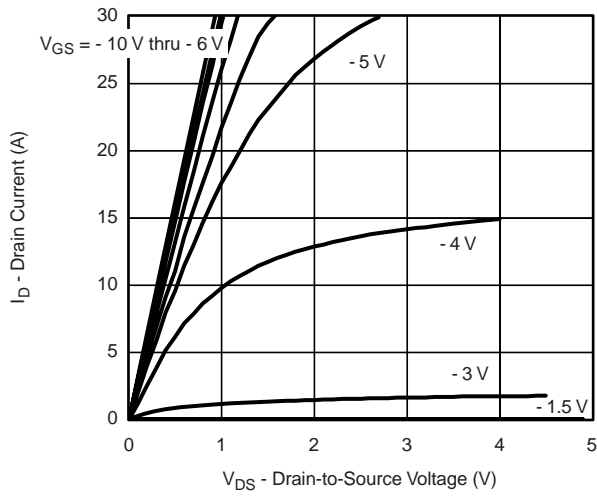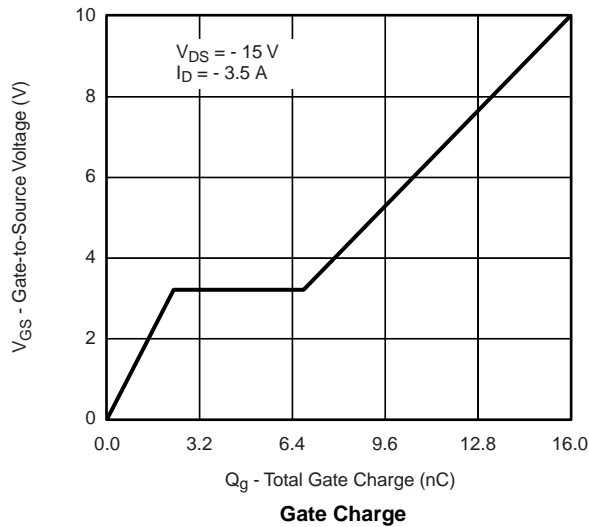


**Output Characteristics**
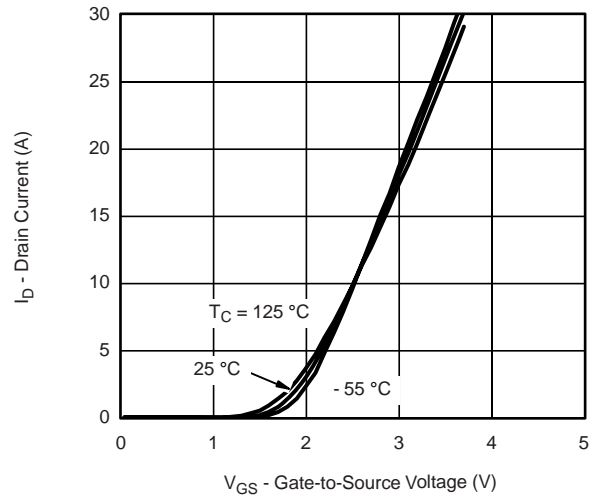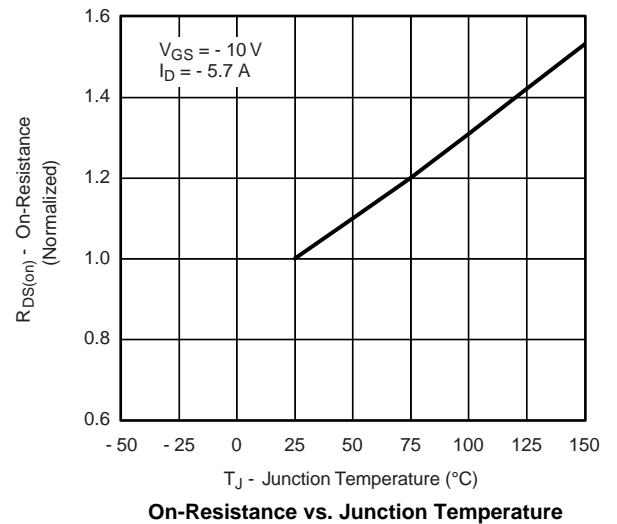


**Transfer Characteristics**



**On-Resistance vs. Drain Current**
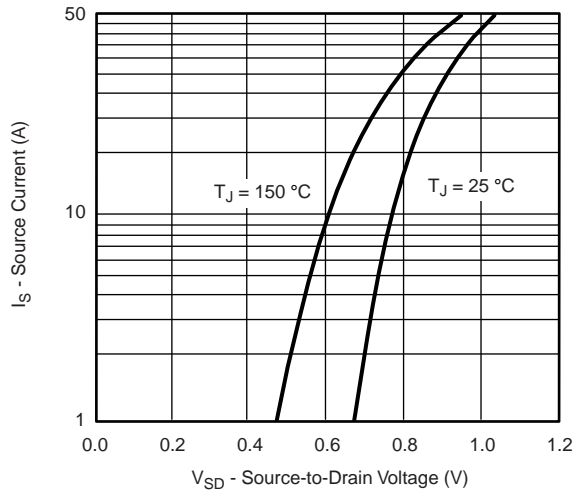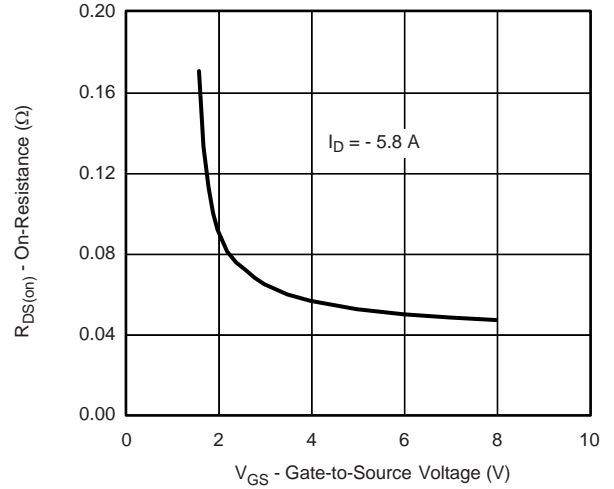


**Capacitance**



**Gate Charge**



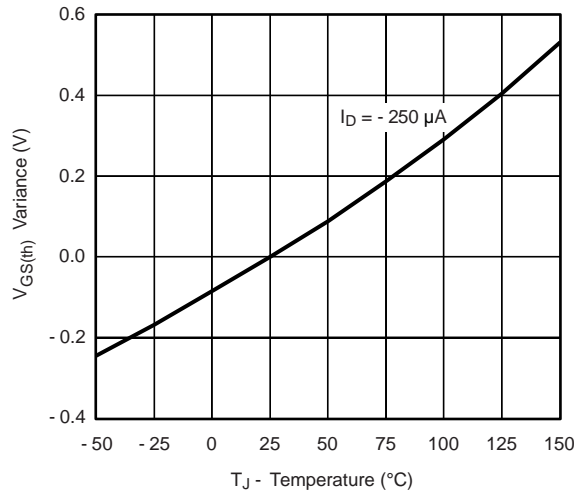**On-Resistance vs. Junction Temperature**

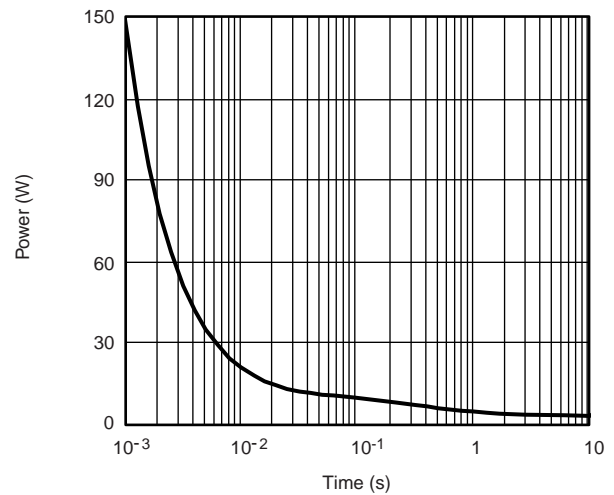**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



**Source-Drain Diode Forward Voltage**



**On-Resistance vs. Gate-to-Source Voltage**



**Threshold Voltage**



**Single Pulse Power, Junction-to-Ambient**
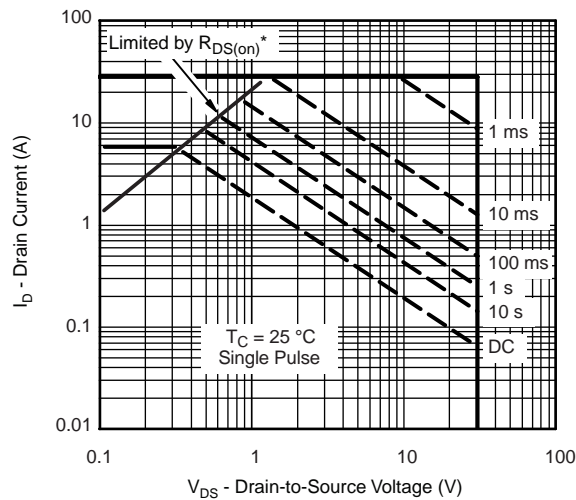


**Safe Operating Area, Junction-to-Foot**

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**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



Notes:

1. Duty Cycle, $D = \dfrac{t_1}{t_2}$
2. Per Unit Base = $R_{thJA}$ = 70 °C/W
3. $T_{JM} - T_A = P_{DM} Z_{thJA}^{(t)}$
4. Surface Mounted
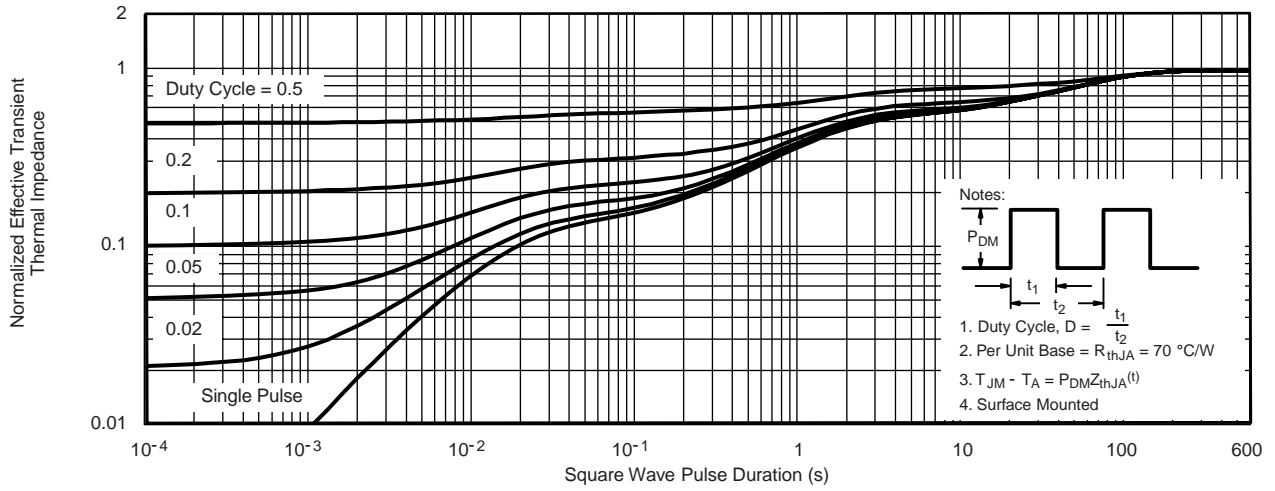
**Normalized Thermal Transient Impedance, Junction-to-Ambient**
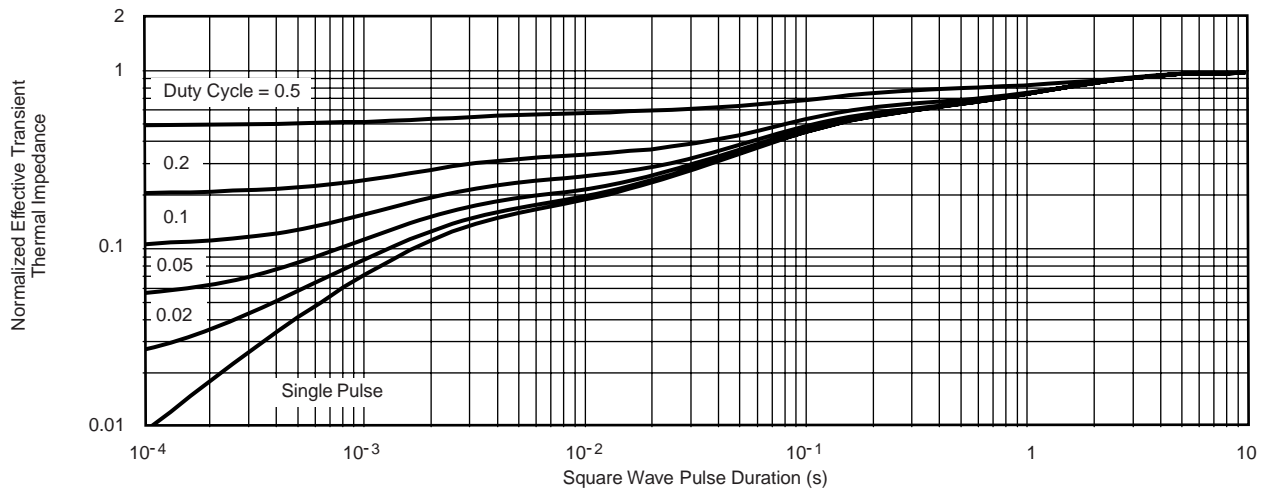


**Normalized Thermal Transient Impedance, Junction-to-Foot**

# SOP-8 PACKAGE OUTLINE

TOP VIEW

SIDE VIEW

SIDE VIEW
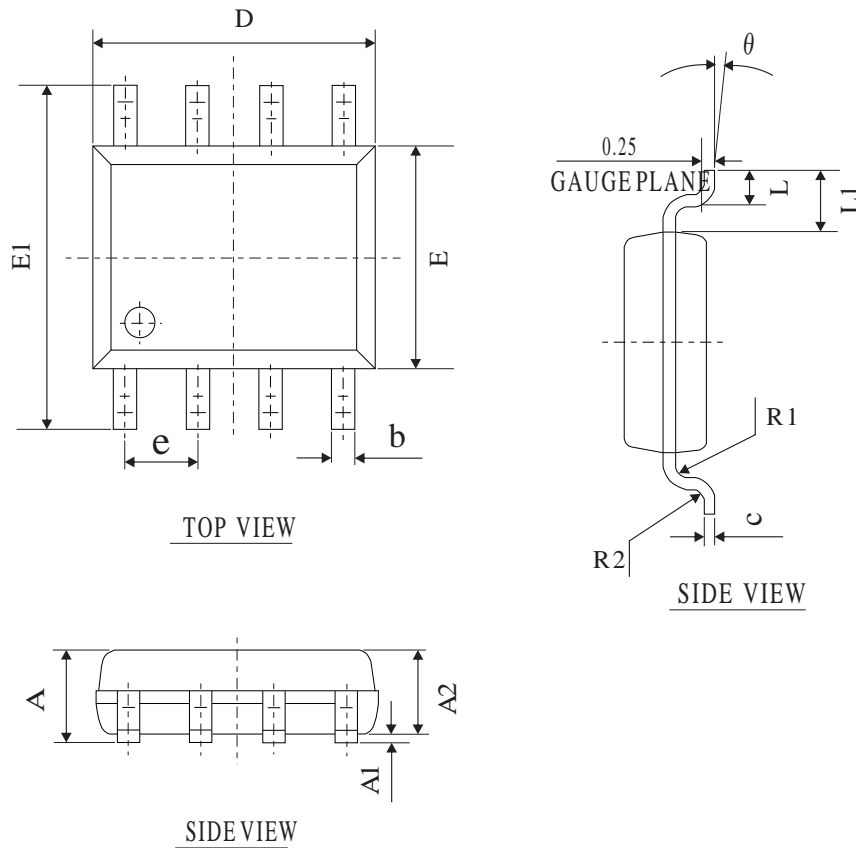
COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

| SYMBOL | MIN | TYP | MAX |
|--------|-----|-----|-----|
| A | 1.30 | 1.60 | 1.85 |
| A1 | 0.03 | 0.15 | 0.28 |
| A2 | 1.20 | 1.45 | 1.70 |
| b | 0.26 | 0.40 | 0.54 |
| C | 0.132 | 0.203 | 0.273 |
| D | 4.50 | 4.90 | 5.30 |
| E | 3.50 | 3.00 | 4.30 |
| E1 | 5.50 | 6.00 | 6.50 |
| L | 0.30 | 0.70 | 1.10 |
| θ | 2° | 4° | 6° |
| L1 | 1.04REF | | |
| e | 1.27BSC | | |
| R1 | 0.07TYP | | |
| R2 | 0.07TYP | | |

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